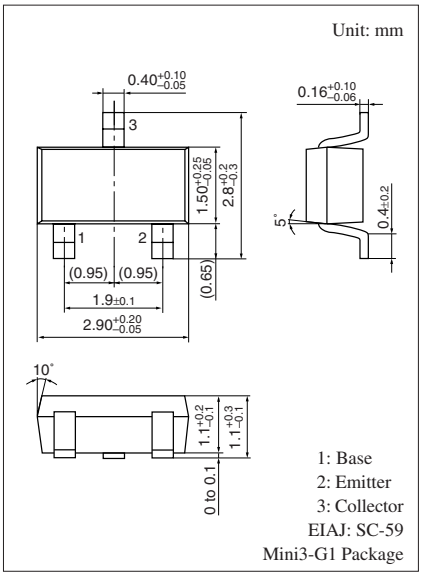
2SC5813

Silicon NPN epitaxial planar type

For DC-DC converter

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing



Marking Symbol: 5H

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	80	V
Collector-emitter voltage (Base open)	V_{CEO}	80	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	1.5	A
Peak collector current	I_{CP}	3	A
Collector power dissipation *	P_C	600	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

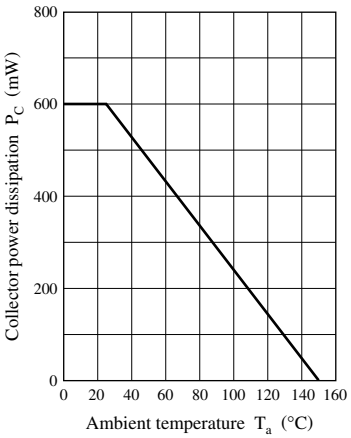
Note) ∗: Measure on the ceramic substrate at 15 mm × 15 mm × 0.6 mm

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

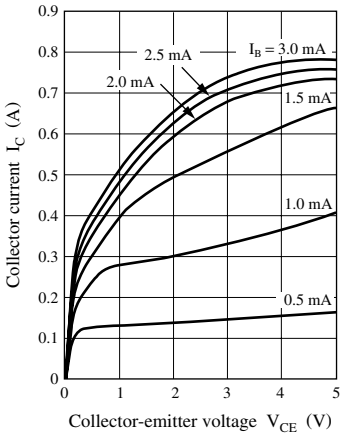
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	I_C = 10 µA, I_E = 0	80			V
Collector-emitter voltage (Base open)	V_{CEO}	I_C = 1 mA, I_B = 0	80			V
Emitter-base voltage (Collector open)	V_{EBO}	I_E = 10 µA, I_C = 0	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	V_{CB} = 40 V, I_E = 0			0.1	µA
Forward current transfer ratio *	h_{FE}	V_{CE} = 2 V, I_C = 100 mA	200			—
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = 1 A, I_B = 20 mA		350	500	mV
Transition frequency	f_T	V_{CB} = 10 V, I_E = −50 mA, f = 200 MHz		180		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz		15	25	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. ∗: Pulse measurement

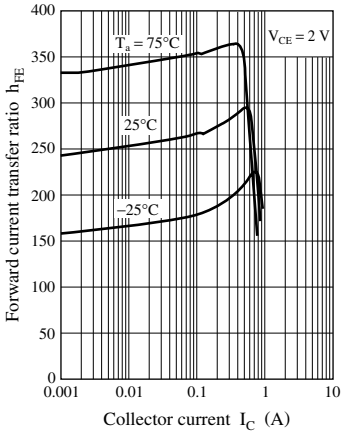
P_C — T_a



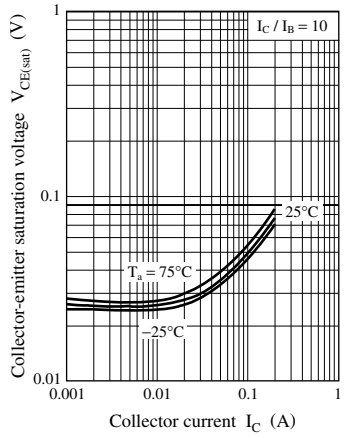
I_C — V_{CE}



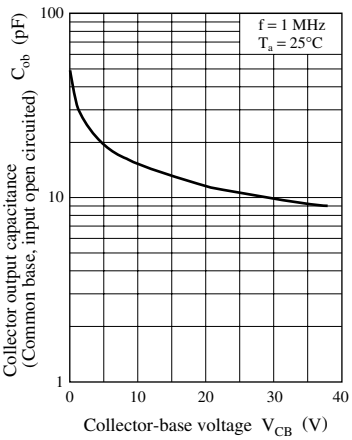
h_{FE} — I_C



$V_{CE(sat)}$ — I_C



C_{ob} — V_{CB}



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